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October 2014



# KSA1013 PNP Epitaxial Silicon Transistor

#### Features

- Color TV Audio Output
- Color TV Vertical Deflection Output



#### **Ordering Information**

Part Number	Top Mark	Package	Packing Method
KSA1013YBU			Bulk
KSA1013OBU	A1013	TO-92 3L	Duik
KSA1013YTA	A1013 10-92 3L	Ammo	
KSA1013OTA			Ammo

### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage	-160	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-160	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V	
۱ <sub>C</sub>	Collector Current	-1	А	
Ι <sub>Β</sub>	Base Current	-0.5	А	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 to +150	°C	

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### Thermal Characteristics<sup>(1)</sup>

Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.

Symbol	Parameter	Value	Unit
P <sub>D</sub>	Power Dissipation	900	mW
	Derate Above $T_A = 25^{\circ}C$	7.2	mW/°C
R <sub>0JA</sub> Thermal Resistance, Junction-to-Ambient		139	°C/W

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

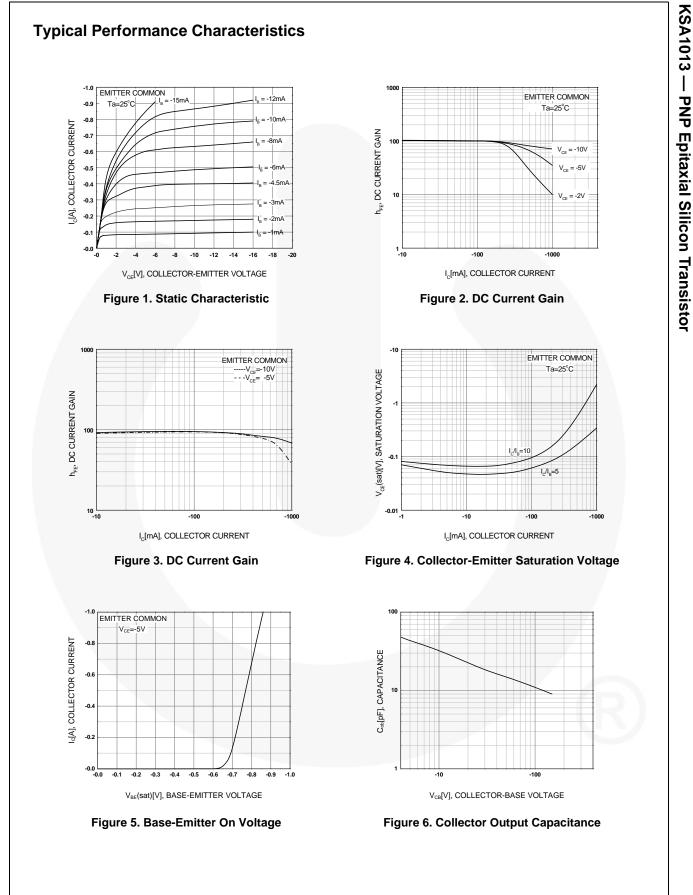
#### **Electrical Characteristics**

Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.

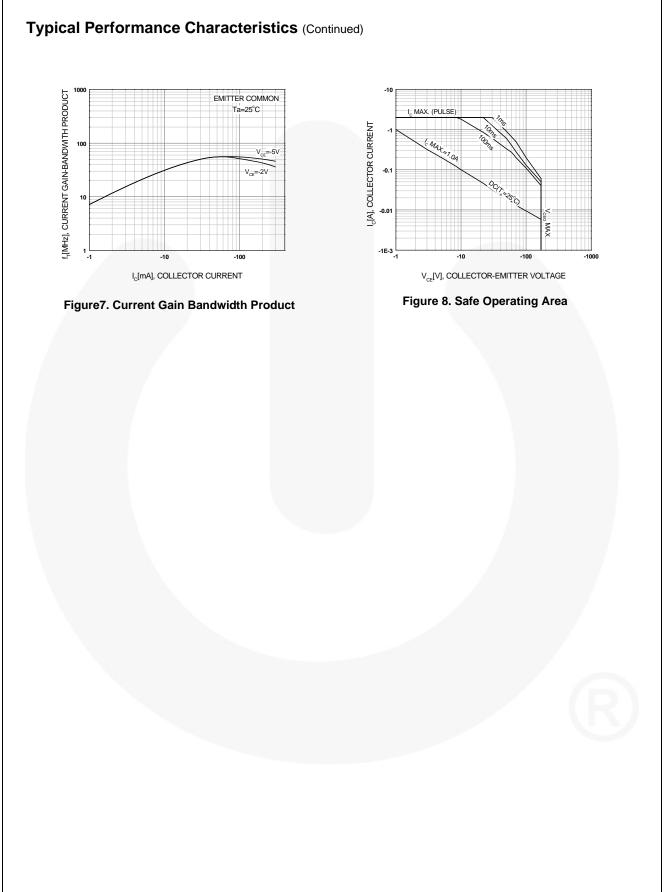
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-Off Current	$V_{CB} = -150 \text{ V}, \text{ I}_{E} = 0$			-1	μA
I <sub>EBO</sub>	Emitter Cut-Off Current	$V_{EB} = -6 V, I_{C} = 0$			-1	μA
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = -10$ mA, $I_{\rm B} = 0$	-160			V
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -5 V, I_{C} = -200 mA$	60		320	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_{\rm C}$ = -500 mA, $I_{\rm B}$ = -50 mA			-1.5	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = -5 V, I_{C} = -5 mA$	-0.45		-0.75	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -200 \text{ mA}$	15	50		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz			35	pF

## h<sub>FE</sub> Classification

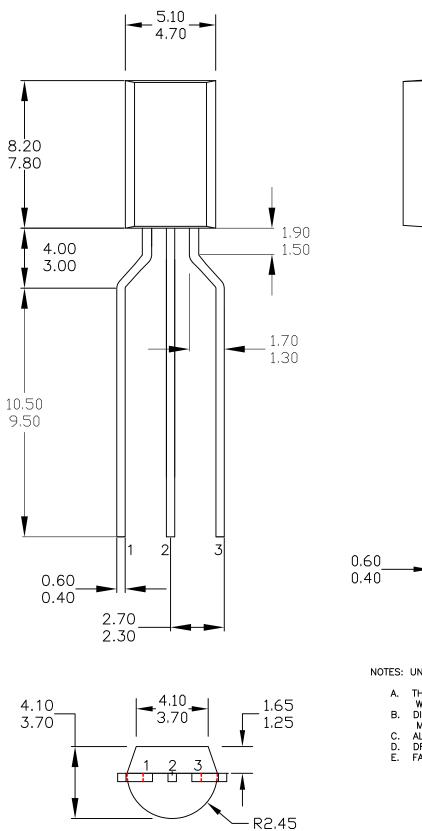
Classification	R	0	Y
h <sub>FE</sub>	60 ~ 120	100 ~ 200	160 ~ 320



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KSA1013 — PNP Epitaxial Silicon Transistor



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